

查詢"BTA212P"供應商  
**Three quadrant triacs**  
**high commutation**

**BTA212 series B**
**GENERAL DESCRIPTION**

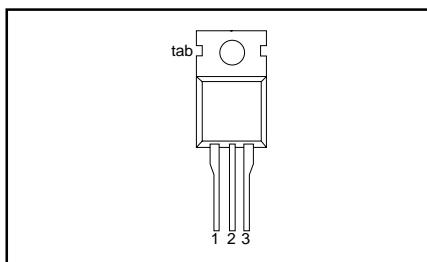
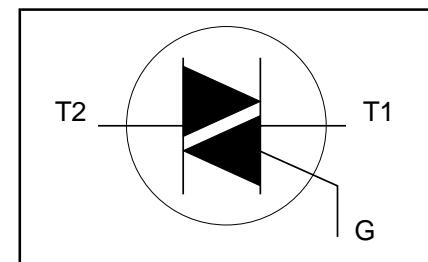
Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic  $dV/dt$  and high  $di/dt$  can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$	BTA212- Repetitive peak off-state voltages	500B 500	600B 600	800B 800	V
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
$I_{TSM}$	Non-repetitive peak on-state current	95	95	95	A

**PINNING - TO220AB**

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

**PIN CONFIGURATION**

**SYMBOL**

**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	-500 500 <sup>1</sup>	-600 600 <sup>1</sup>	-800 800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99^\circ C$	-	12			A
$I_{TSM}$	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ C$ prior to surge					
$I^2t$ $dl_T/dt$	$I^2t$ for fusing Repetitive rate of rise of on-state current after triggering	$t = 20$ ms $t = 16.7$ ms $t = 10$ ms $I_{TM} = 20$ A; $I_G = 0.2$ A; $dl_G/dt = 0.2$ A/ $\mu$ s	- - - -	95	105	100	A A A <sup>2</sup> S A/ $\mu$ s
$I_{GM}$ $V_{GM}$ $P_{GM}$ $P_{G(AV)}$	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms period	- - - -	2	5	5	A V W W
$T_{stg}$ $T_j$	Storage temperature Operating junction temperature		-40 -	150	125		°C °C

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu$ s.

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## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\cdot mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.5	K/W
$R_{th\ j\cdot a}$	Thermal resistance junction to ambient	half cycle in free air	-	60	2.0	K/W

## STATIC CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{GT}$	Gate trigger current <sup>2</sup>	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	2	18	50	mA
$I_L$	Latching current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	2	21	50	mA
$I_H$	Holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	2	34	50	mA
$V_T$	On-state voltage	$I_T = 17\text{ A}$	-	31	60	mA
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	34	90	mA
$I_D$	Off-state leakage current	$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125^\circ\text{C}$	-	30	60	mA
		$V_D = V_{DRM(max)}$ ; $T_j = 125^\circ\text{C}$	0.25	31	60	mA
			-	1.3	1.6	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$	-	0.7	1.5	V
		$V_D = V_{DRM(max)}$ ; $T_j = 125^\circ\text{C}$	-	0.4	-	V
			-	0.1	0.5	mA

## DYNAMIC CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125^\circ\text{C}$ ; exponential waveform; gate open circuit	1000	4000	-	V/ $\mu\text{s}$
$dl_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $I_{T(RMS)} = 12\text{ A}$ ; without snubber; gate open circuit	-	24	-	A/ms
$t_{gt}$	Gate controlled turn-on time	$I_{TM} = 12\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1\text{ A}$ ; $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$

**2** Device does not trigger in the T2-, G+ quadrant.

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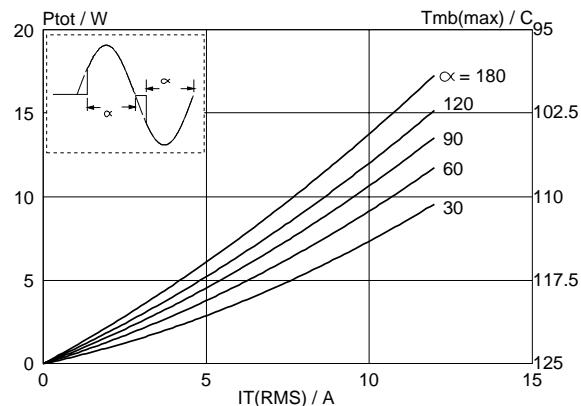


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

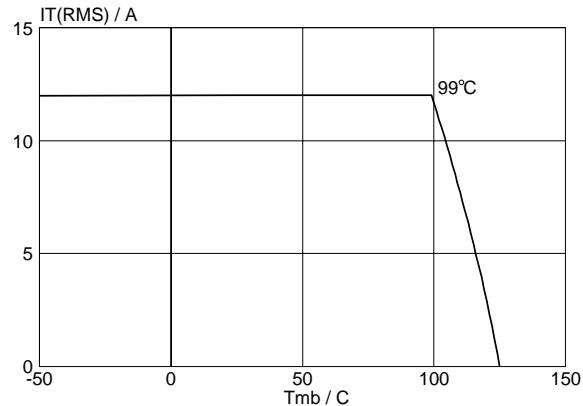


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

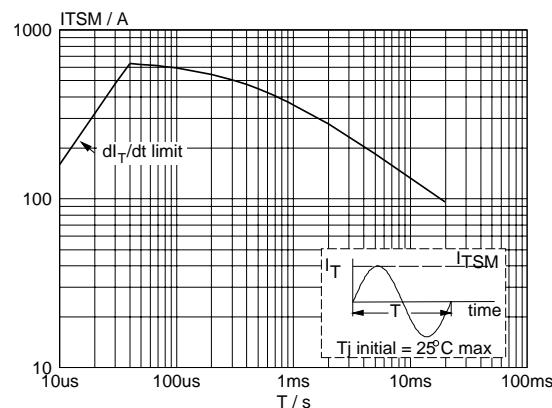


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20ms$ .

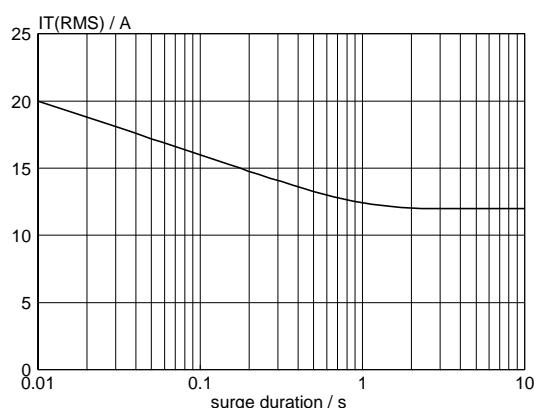


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50$  Hz;  $T_{mb} \leq 99$  °C.

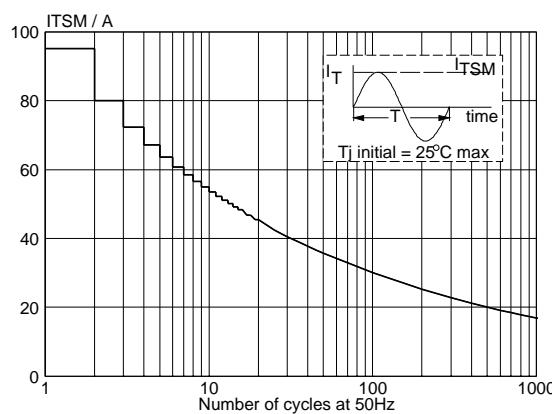


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50$  Hz.

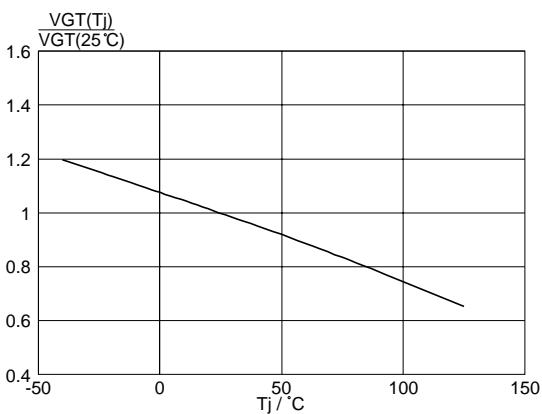


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ C)$ , versus junction temperature  $T_j$ .

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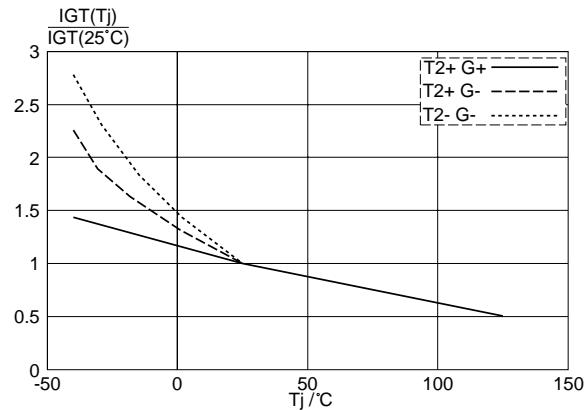


Fig.7. Normalised gate trigger current  $I_{GT}(T_j)/I_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

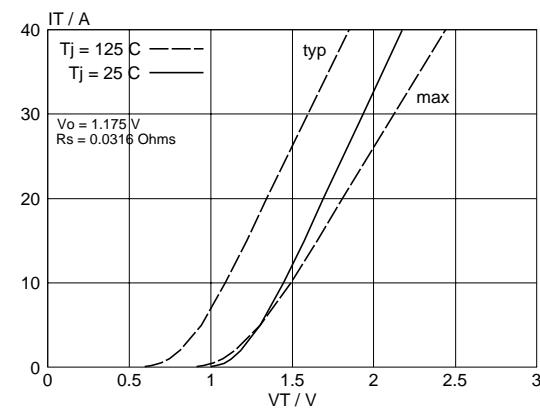


Fig.10. Typical and maximum on-state characteristic.

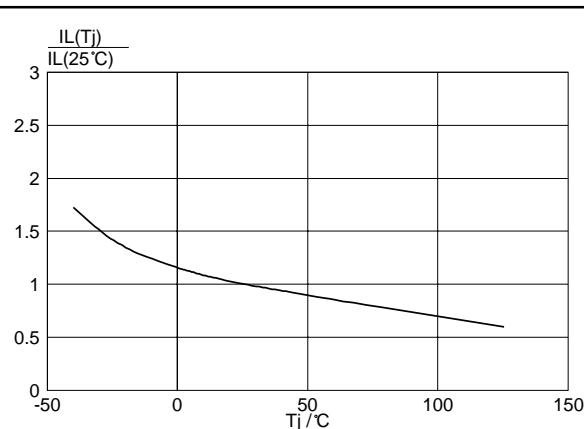


Fig.8. Normalised latching current  $I_L(T_j)/I_L(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

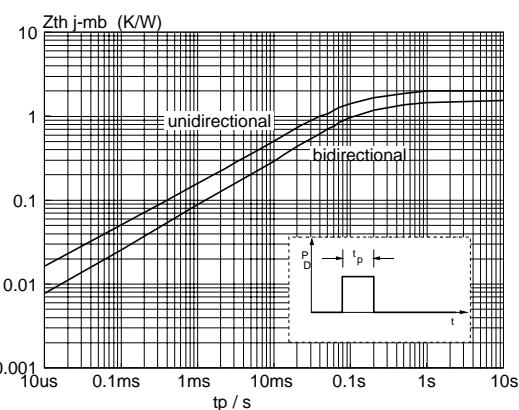


Fig.11. Transient thermal impedance  $Z_{th,j-mb}$ , versus pulse width  $t_p$ .

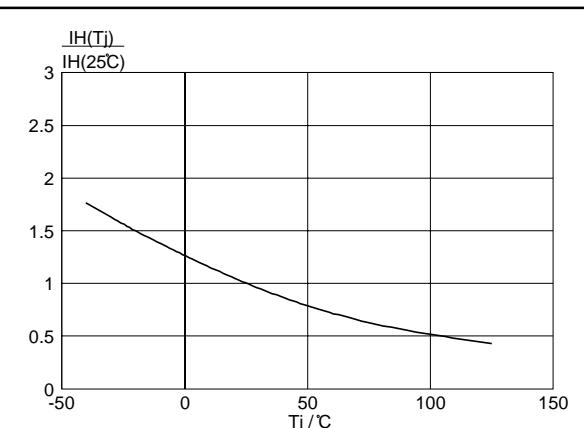


Fig.9. Normalised holding current  $I_H(T_j)/I_H(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

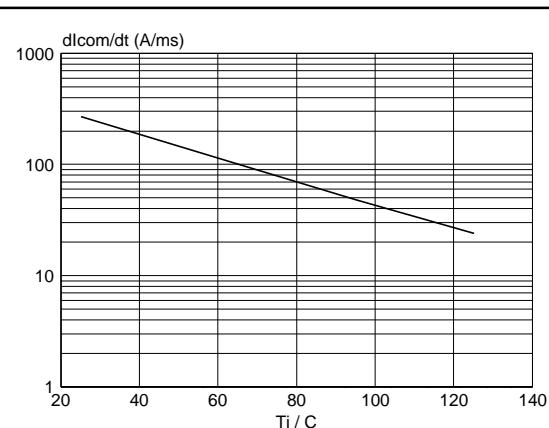


Fig.12. Typical, critical rate of change of commutating current  $dl_{com}/dt$  versus junction temperature.

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## MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

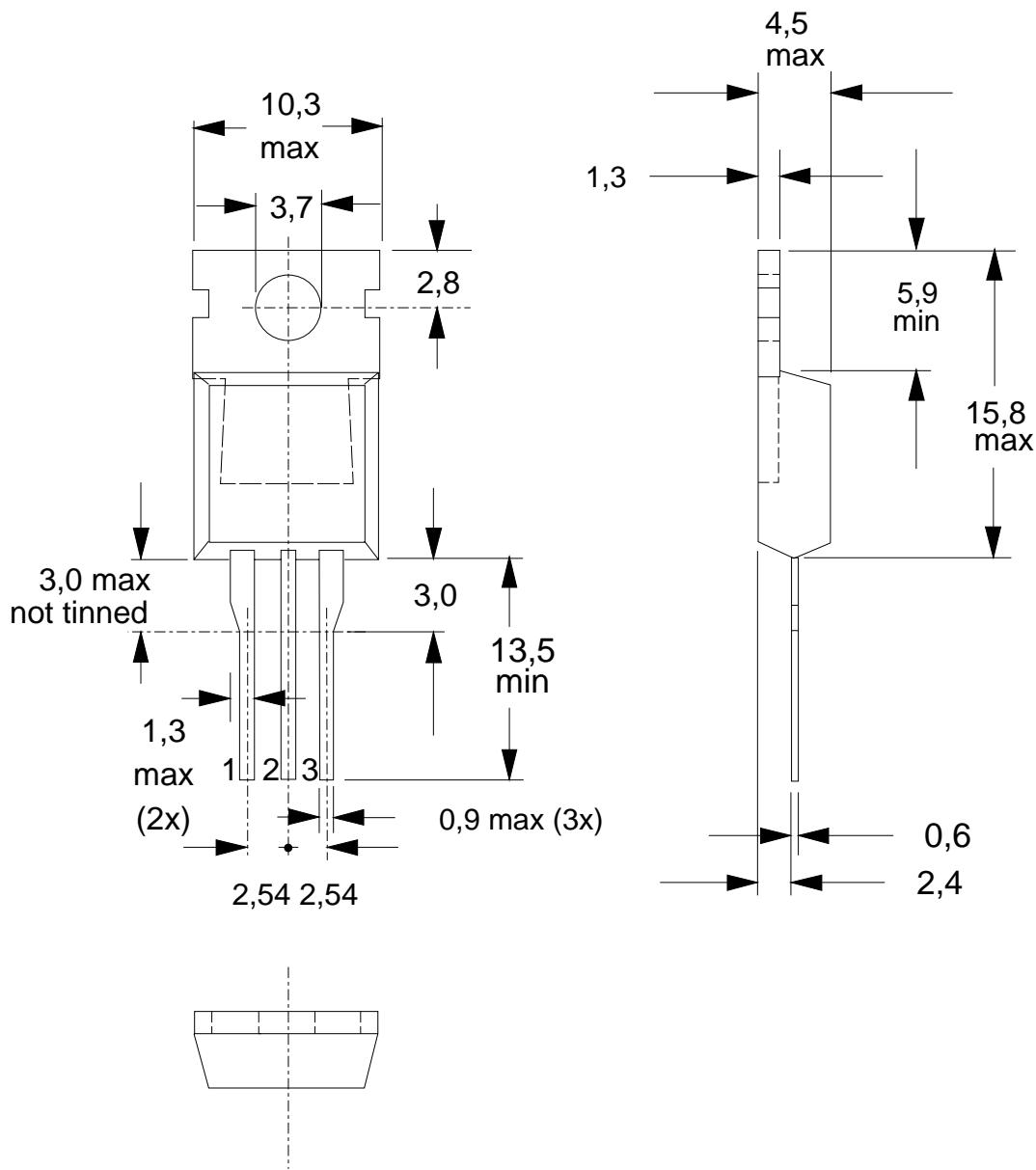


Fig.13. TO220AB; pin 2 connected to mounting base.

## Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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## DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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